Jin Soo Kim

List of Publications by Year
in descending order

72	617	567281 15	752698 20
papers	citations	h-index	g-index

73	73	73	768
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Remoteâ€Controllable Molecular Knob in the Mesomorphic Helical Superstructures. Advanced Functional Materials, 2016, 26, 4242-4251.	14.9	34
2	Interfacial Engineering for the Synergistic Enhancement of Thermal Conductivity of Discotic Liquid Crystal Composites. ACS Applied Materials & Interfaces, 2018, 10, 3155-3159.	8.0	33
3	Perovskite-Based Artificial Multiple Quantum Wells. Nano Letters, 2019, 19, 3535-3542.	9.1	27
4	Influences of Si-doped graded short-period superlattice on green InGaN/GaN light-emitting diodes. Optics Express, 2016, 24, 7743.	3.4	26
5	A UV-responsive pressure sensitive adhesive for damage-free fabrication of an ultrathin imperceptible mechanical sensor with ultrahigh optical transparency. Journal of Materials Chemistry A, 2019, 7, 22588-22595.	10.3	25
6	Application of Hexagonal Boron Nitride to a Heat-Transfer Medium of an InGaN/GaN Quantum-Well Green LED. ACS Applied Materials & Interfaces, 2019, 11, 18876-18884.	8.0	25
7	Photopolymerization of Reactive Amphiphiles: Automatic and Robust Vertical Alignment Layers of Liquid Crystals with a Strong Surface Anchoring Energy. Macromolecules, 2016, 49, 23-29.	4.8	24
8	Highly Efficient and Flexible Photosensors with GaN Nanowires Horizontally Embedded in a Graphene Sandwich Channel. ACS Applied Materials & Interfaces, 2018, 10, 38173-38182.	8.0	22
9	Fast Response Characteristics of Flexible Ultraviolet Photosensors with GaN Nanowires and Graphene. ACS Applied Materials & Interfaces, 2020, 12, 970-979.	8.0	22
10	Polarized Light Emission from Uniaxially Oriented and Polymer-Stabilized AIE Luminogen Thin Films. Macromolecules, 2019, 52, 1739-1745.	4.8	20
11	Topochemical polymerization of dumbbell-shaped diacetylene monomers: relationship between chemical structure, molecular packing structure, and gelation property. Soft Matter, 2017, 13, 5759-5766.	2.7	19
12	Highly Efficient Photoelectrochemical Water Splitting Using GaN-Nanowire Photoanode with Tungsten Sulfides. ACS Applied Materials & Interfaces, 2020, 12, 58028-58037.	8.0	18
13	Structural and electrical properties of catalyst-free Si-doped InAs nanowires formed on Si(111). Scientific Reports, 2015, 5, 16652.	3.3	16
14	Hydrogen Generation using non-polar coaxial InGaN/GaN Multiple Quantum Well Structure Formed on Hollow n-GaN Nanowires. Scientific Reports, 2016, 6, 31996.	3.3	16
15	Growth and characterization of seed layer-free ZnO thin films deposited on porous silicon by hydrothermal method. Electronic Materials Letters, 2012, 8, 75-80.	2.2	15
16	Stretchable Inorganic GaN-Nanowire Photosensor with High Photocurrent and Photoresponsivity. ACS Applied Materials & Interfaces, 2021, 13, 22728-22737.	8.0	15
17	Effects of a thin InGaAs layer on carrier dynamics of InAs quantum dots. Journal of Applied Physics, 2010, 108, 093521.	2.5	13
18	Structural, optical, and electrical properties of ZnO thin films deposited by sol-gel dip-coating process at low temperature. Electronic Materials Letters, 2014, 10, 869-878.	2.2	12

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19	Influences of graded superlattice on the electrostatic discharge characteristics of green InGaN/GaN light-emitting diodes. Journal of Crystal Growth, 2017, 464, 138-142.	1.5	11
20	Enhanced optical output in InGaN/GaN light-emitting diodes by tailored refractive index of nanoporous GaN. Nanotechnology, 2019, 30, 415301.	2.6	11
21	Room-temperature operation of light-assisted NO₂ gas sensor based on GaN nanowires and graphene. Nanotechnology, 2021, 32, 505201.	2.6	10
22	Optical stability of shape-engineered InAs/InAlGaAs quantum dots. Journal of Applied Physics, 2009, 105, 053510.	2.5	9
23	Effect of different sol concentrations on the properties of nanocrystalline ZnO thin films grown on FTO substrates by sol-gel spin-coating. Journal of the Korean Physical Society, 2014, 65, 480-486.	0.7	9
24	K-doping effects on the characteristics of ZnO thin films synthesized by using a spin-coating method. Journal of the Korean Physical Society, 2014, 64, 1581-1585.	0.7	9
25	Optical properties of the InAs/InAlGaAs quantum dots subjected to thermal treatments. Thin Solid Films, 2010, 518, 6429-6431.	1.8	8
26	Effects of in doping on structural and optical properties of ZnO nanorods grown by hydrothermal method. Electronic Materials Letters, 2013, 9, 509-512.	2.2	8
27	Improvement of Terahertz Wave Radiation for InAs Nanowires by Simple Dipping into Tap Water. Scientific Reports, 2016, 6, 36094.	3.3	8
28	Improvement in the photoelectrochemical water-splitting performance using GaN nanowires with bundle structures. Journal of Materials Chemistry C, 2021, 9, 12802-12810.	5.5	8
29	Photoelectrochemical Water Splitting using GaN Nanowires with Reverse-Mesa Structures as Photoanode Material. Applied Science and Convergence Technology, 2022, 31, 51-55.	0.9	8
30	Drastic improvement in photoelectrochemical water splitting performance over prolonged reaction time using new carrier-guiding semiconductor nanostructures. Journal of Materials Chemistry A, 2022, 10, 9821-9829.	10.3	8
31	Dependence of Internal Crystal Structures of InAs Nanowires on Electrical Characteristics of Field Effect Transistors. Journal of Electronic Materials, 2018, 47, 944-948.	2.2	7
32	Formation Mechanism of GaN Nanowires with Various Shapes on Si(111). Journal of the Korean Physical Society, 2020, 77, 247-252.	0.7	7
33	Photoelectrochemical water-splitting using GaN pyramidal dots and their long-term stability in the two-electrode configuration. Journal of Materials Chemistry A, 2022, 10, 10355-10362.	10.3	7
34	Effects of growth conditions on the structural and the optical properties of ZnO submicron particles grown by using vapor phase transport. Journal of the Korean Physical Society, 2012, 60, 1599-1604.	0.7	6
35	Effects of Ga concentration on the structural, electrical and optical properties of Ga-doped ZnO thin films grown by sol-gel method. Journal of the Korean Physical Society, 2014, 64, 109-113.	0.7	6
36	Yellow-red light-emitting diodes using periodic Ga-flow interruption during deposition of InGaN well. Optics Express, 2017, 25, 15152.	3.4	6

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37	Effects of band-offset on the carrier lifetime in InAs quantum dots on InP substrates. Journal of Applied Physics, 2007, 101, 096103.	2.5	5
38	Different shape of GaAs quantum structures under various growth conditions. Thin Solid Films, 2010, 518, 6500-6504.	1.8	5
39	Carrier repopulation process for spatially-ordered InAs/InAlGaAs quantum dots. Journal of Applied Physics, 2011, 109, 113505.	2.5	5
40	Effects of post-heat-treatment temperature for seed layers on the properties of ZnO nanostructures grown by using the hydrothermal method. Journal of the Korean Physical Society, 2012, 60, 1593-1598.	0.7	5
41	Optimizing the optical properties of fluorine-doped ZnO thin films deposited by sol-gel spin-coating. Journal of the Korean Physical Society, 2014, 65, 509-514.	0.7	5
42	Flower-Like Internal Emission Distribution of LEDs with Monolithic Integration of InGaN-based Quantum Wells Emitting Narrow Blue, Green, and Red Spectra. Scientific Reports, 2017, 7, 7164.	3.3	5
43	Structural and Optical Properties of GaN Nanowires Formed on Si(111). Applied Science and Convergence Technology, 2018, 27, 95-99.	0.9	5
44	1.55 mum InAs/InAlGaAs Quantum Dot DFB Lasers. IEEE Nanotechnology Magazine, 2008, 7, 128-130.	2.0	4
45	Optical parameters of Mg x Zn1â^'x O thin films prepared by using the sol-gel method. Journal of the Korean Physical Society, 2012, 60, 830-835.	0.7	4
46	Spatial emission distribution of InGaN/GaN light-emitting diodes depending on the pattern structures. Materials Research Bulletin, 2014, 58, 121-125.	5.2	4
47	Formation of spherical-shaped GaN and InN quantum dots on curved SiN/Si surface. Nanotechnology, 2018, 29, 315603.	2.6	4
48	Temperature dependence of the optical properties of high-density GaAs quantum dots. Journal of the Korean Physical Society, 2012, 60, 1428-1432.	0.7	3
49	Effects of growth temperature on the structural and the optical properties of ZnO thin films on porous silicon grown by using plasma-assisted molecular beam epitaxy. Journal of the Korean Physical Society, 2012, 60, 1570-1575.	0.7	3
50	Effects of zinc capping layers and annealing on the properties of porous silicon. Journal of the Korean Physical Society, 2012, 60, 1582-1586.	0.7	3
51	Photoluminescent properties of Cd x Zn1â^'x O thin films prepared by sol-gel spin-coating method. Electronic Materials Letters, 2013, 9, 497-500.	2.2	3
52	Growth and optical properties of sol-gel ZnO thin films grown on R-plane sapphire substrates. Journal of the Korean Physical Society, 2013, 62, 1154-1159.	0.7	3
53	Luminescence properties of InGaN/GaN light-emitting diodes with violet, blue, and green emission. Journal of the Korean Physical Society, 2021, 78, 275-279.	0.7	3
54	Effects of post-annealing temperature on the properties of ZnO nanorods grown on homogenous seed-layers by using the hydrothermal method. Journal of the Korean Physical Society, 2012, 60, 1605-1610.	0.7	2

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55	Formation characteristics of a self-catalyzed GaAs nanowire without a Ga droplet on Si(111). Journal of the Korean Physical Society, 2012, 61, 2017-2021.	0.7	2
56	Modification in the structural and optical characteristics of InAs quantum dots by manipulating the strain distribution. Journal of the Korean Physical Society, 2012, 60, 460-465.	0.7	2
57	Influences of dot-in-a-well structure and GaAs insertion layer on InP-based InAs quantum dots. Journal of the Korean Physical Society, 2013, 62, 1274-1279.	0.7	2
58	Improved Hole Transport by ${m p}hbox{-}{m In}_{x}{m Ga}_{1-x}{m N}$ Layer in Multiple Quantum Wells of Visible LEDs. IEEE Photonics Technology Letters, 2013, 25, 1789-1792.	2.5	2
59	Influence of Cr-doping on the structural and the optical properties of ZnO thin films prepared by sol-gel spin coating. Journal of the Korean Physical Society, 2014, 64, 41-45.	0.7	2
60	Luminescence Properties of InGaN/GaN Green Light-Emitting Diodes with Si-Doped Graded Short-Period Superlattice. Journal of Nanoscience and Nanotechnology, 2021, 21, 5648-5652.	0.9	2
61	Wavelength Shift of InP-Based InAs Quantum Dot Lasers Above Room Temperature. Journal of Nanoscience and Nanotechnology, 2007, 7, 4443-4446.	0.9	1
62	Investigation on the lasing characteristics of InAs/InGaAsP quantum dots with additional confinement structures. Journal of Crystal Growth, 2014, 393, 59-63.	1.5	1
63	Periodic variation in the electroluminescence intensity on a single pattern from InGaN/GaN light-emitting diodes fabricated on lens-shaped patterns. Journal of the Korean Physical Society, 2015, 66, 266-269.	0.7	1
64	Emission characteristics of shape-engineered InAs/InAlGaAs quantum dots subjected to thermal treatments. Journal of the Korean Physical Society, 2016, 69, 85-90.	0.7	1
65	Improvement of device performances, including electrostatic discharge characteristics, of InGaN/GaN light-emitting diodes by using a Si-doped graded superlattice. Journal of the Korean Physical Society, 2017, 70, 1001-1006.	0.7	1
66	Flexible 1.3 Î¼m photodetector fabricated with InN nanowires and graphene on overhead projector transparency sheet. Nanoscale, 2022, 14, 10793-10800.	5.6	1
67	Improved blue electroluminescence in InGaN/GaN multiple-quantum well light-emitting diodes with an electron blocking layer. Journal of the Korean Physical Society, 2013, 62, 1160-1163.	0.7	0
68	Analysis of the abnormal voltage-current behaviors on localized carriers of InGaN/GaN multiple quantum well from electron blocking layer. Journal of the Korean Physical Society, 2013, 63, 1784-1788.	0.7	0
69	Spatially resolved optical properties of ZnO sub-microstructures on a graphene monolayer. Journal of the Korean Physical Society, 2015, 67, 1634-1638.	0.7	0
70	Terahertz characteristics of InGaAs with periodically-positioned InAlAs insertion layers. , 2015, , .		0
71	Flower-like light distribution inside InGaN-based light-emitting diodes operated in spectral range from violet to red. , 2017, , .		0
72	Terahertz Characteristics of InGaAs with Periodic InAlAs Insertion Layers. Applied Science and Convergence Technology, 2018, 27, 173-177.	0.9	0